

4. (original) An apparatus according to claim 1, wherein the magnet is a permanent magnet.
5. (original) An apparatus according to claim 1, wherein the magnet is an electromagnet.
6. (original) An apparatus according to claim 1, wherein said structure is of a material susceptible to erosion during the plasma processing, so that the magnetic field reduces said erosion.
7. (original) An apparatus according to claim 1, wherein said structure is of a material selected from the group consisting of quartz, silicon, Y_2O_3 , silicon carbide and Al_2O_3 .
8. (new) An apparatus according to claim 1, wherein the magnetic field is axisymmetric.
9. (new) An apparatus according to claim 8, wherein the strength of the magnetic field is higher than 200G, the strength of the magnetic field reflect the plasma away from the edges of the wafer.